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FAIRCHILD SEMICONDUCTOR CORPORATION

UNITED STATES DISTRICT COURT
FOR THE NORTHERN DISTRICT OF CALIFORNIA
SAN FRANCISCO DIVISION

ALPHA & OMEGA SEMICONDUCTOR,
INC., a California corporation; and
ALPHA & OMEGA SEMICONDUCTOR,
LTD., a Bermuda corporation,

Plaintiffs and Counterdefendants,

v.

FAIRCHILD SEMICONDUCTOR
CORP., a Delaware corporation,

Defendant and Counterclaimant.

Case No. C 07-2638 JSW (EDL)
(Consolidated with Case No. C 07-2664 JSW)

**[PROPOSED] ORDER DENYING
PLAINTIFFS' MOTION TO COMPEL
RESPONSES TO INTERROGATORIES
AND PRODUCTION OF DOCUMENTS**

Date: December 18, 2007
Time: 9:00 a.m.
Ctroom: Courtroom E, 15th Floor
Judge: Hon. Elizabeth D. Laporte

AND RELATED COUNTERCLAIMS.

1 Plaintiff's Motion to Compel Responses to Interrogatories and Production of Documents was
2 heard before this Court on December 18, 2007.. The Court, having read and considered the supporting
3 and opposing papers, the court file in this case and all other matters presented to the Court, and having
4 considered the arguments of counsel, and good cause appearing therefor, hereby ORDERS:

5 Plaintiff's Motion to Compel Responses to Interrogatories and Production of Documents is
6 DENIED.

7 The Court adopts the following definition of "Accused Fairchild Device" for the purposes of
8 discovery requests:

9
10 The term "Accused Fairchild Device" shall mean any device which includes a power
11 MOSFET made, used, offered for sale, or imported into the United States by Fairchild
that comprises one or more of the following:

12 (a) any IC that includes a source contact area that is divided by at least one gate
13 runner into two or more subcontact areas, and wherein each of the subcontact
areas is connected to a lead-frame by more than one lead-wire; and/or

14 (b) devices made by a method in which a body region is formed adjacent to a
15 trench, a source region is formed in the body region, and an implant is made
16 into the body region of the same conductivity type as the source and which is
other than an implant used to form the source; and/or

17 (c) MOSFET transistors having a body region formed through three dopant
18 implants.

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20 Dated: _____

Honorable Elizabeth D. Laporte

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